

Schottky Barrier Rectifier

MBR20120CT

FEATURES

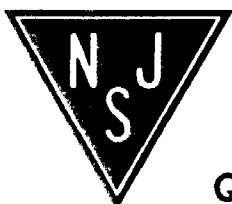
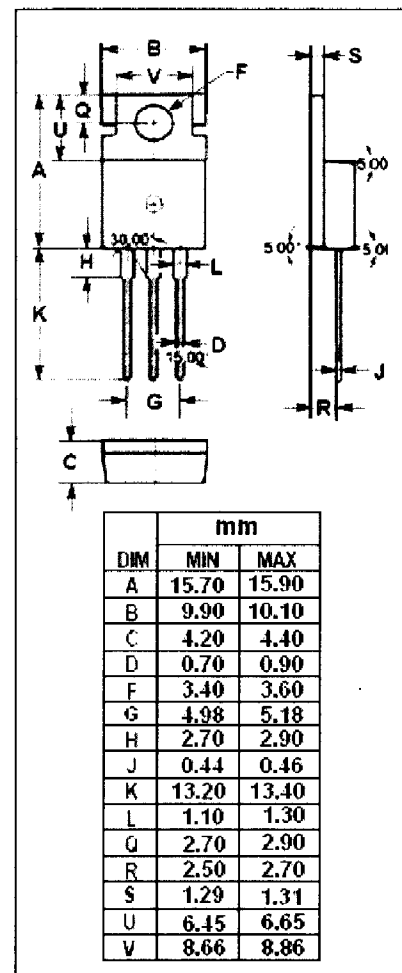
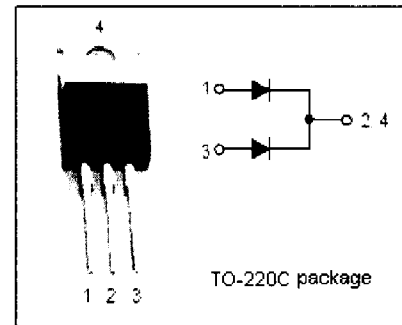
- Low Forward Voltage
- 170°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction
- Dual Rectifier Conduction, Positive Center Tap

MECHANICAL CHARACTERISTICS

- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{RRM}	DC Blocking Voltage	120	V
$I_{F(AV)}$	Average Rectified Forward Current (Rated V_R) $T_C=133^\circ\text{C}$	10	A
I_{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	250	A
T_J	Junction Temperature	170	°C
T_{stg}	Storage Temperature Range	-50~170	°C



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.0	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	60	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s, Duty Cycle \leq 2%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 10A ; T_C = 25^{\circ}C$	0.92	V
I_R	Maximum Instantaneous Reverse Current	$V_R = 120V, T_C = 25^{\circ}C$	10	μA